

## Description

The XXW13P10 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

It is ESD protected.

## General Features

$V_{DS} = -100V, I_D = -13A$

$R_{DS(ON)} < 170m @ V_{GS} = -10V$  (Typ:145m )

Super high dense cell design

Advanced trench process technology

Reliable and rugged

High density cell design for ultra low on-resistance

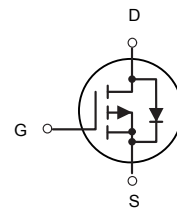
## Application

Power switch

DC/DC converters



**TO252-2L**



P-Channel MOSFET

## Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-13	A
Drain Current-Continuous( $T_c = 100^\circ C$ )	$I_D(100^\circ C)$	-9.2	A
Pulsed Drain Current	$I_{DM}$	-30	A
Maximum Power Dissipation	$P_D$	40	W
Derating factor		0.32	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	$E_{AS}$	110	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

**Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta jc}$	3.13	$^{\circ}C/W$
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**Electrical Characteristics ( $T_c=25^{\circ}C$  unless otherwise noted)**

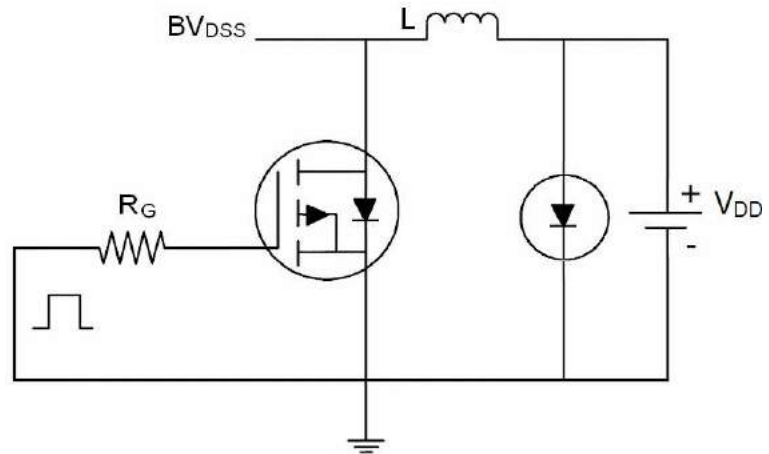
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-100	-	-	V
Zero Gate Voltage Drain Current	$I_{BSS}$	$V_{DS}=-100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1		-3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-16A$	-	145	175	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-15V, I_D=-5A$	12	-	-	S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-25V, V_{GS}=0V,$ $F=1.0MHz$	-	760	-	PF
Output Capacitance	$C_{oss}$		-	260	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	170	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-50V, I_D=-10A$ $V_{GS}=-10V, R_{GEN}=9.1$	-	14	-	nS
Turn-on Rise Time	$t_r$		-	18	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	50	-	nS
Turn-Off Fall Time	$t_f$		-	18	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-50V, I_D=-10A,$ $V_{GS}=-10V$	-	25	-	nC
Gate-Source Charge	$Q_{gs}$		-	5	-	nC
Gate-Drain Charge	$Q_{gd}$		-	7	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-10A$	-	-	-1.2	V
Diode Forward Current (Note 2)	$I_S$	-	-	-	-13	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}C, I_F = -10A$ $di/dt = 100A/\mu s$ (Note3)	-	35	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	46	-	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

**Notes:**

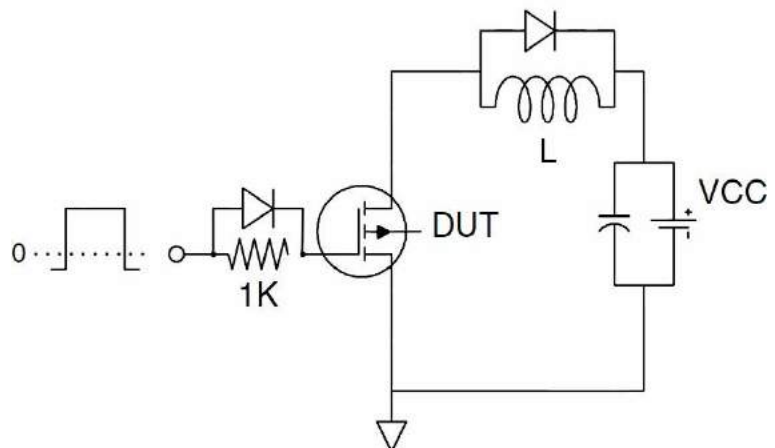
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5.  $E_{AS}$  condition:  $T_J=25^{\circ}C, V_{DD}=-50V, V_G=-10V, L=0.5mH, R_g=25$

**Test Circuit**

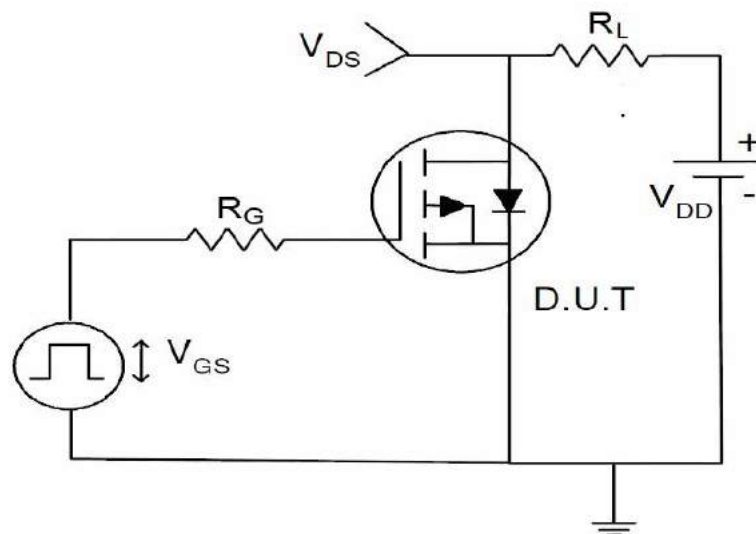
**1) EAS Test Circuit**

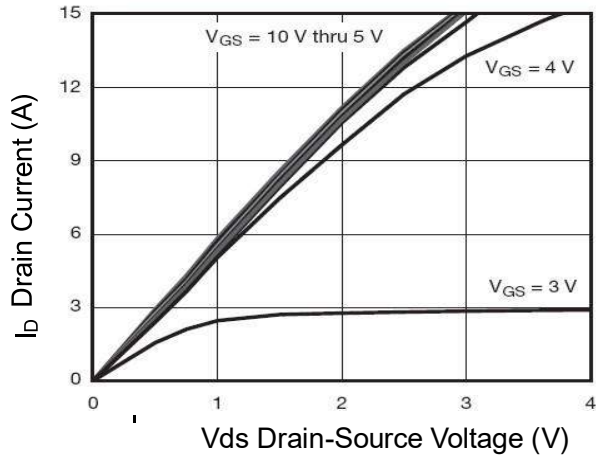
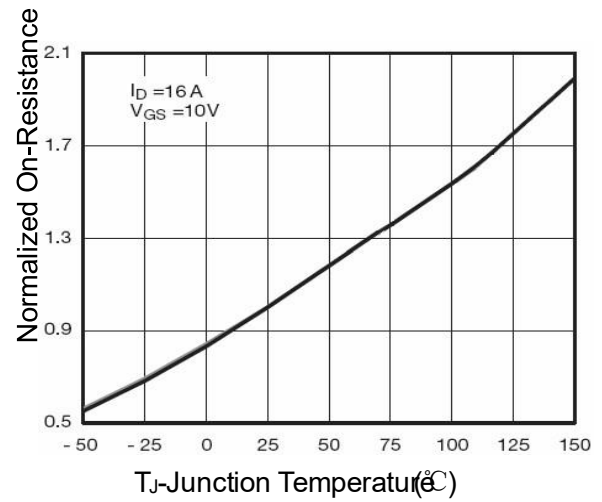
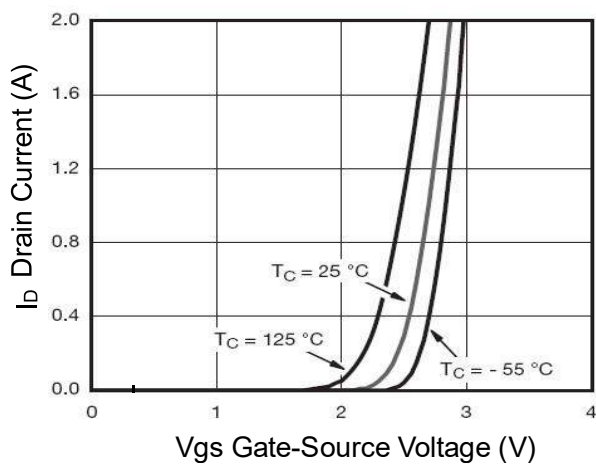
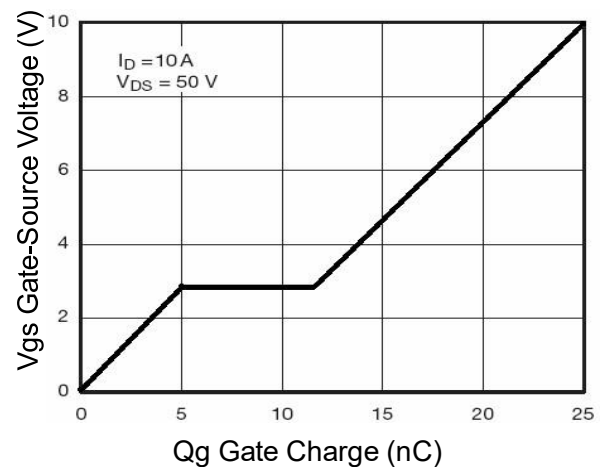
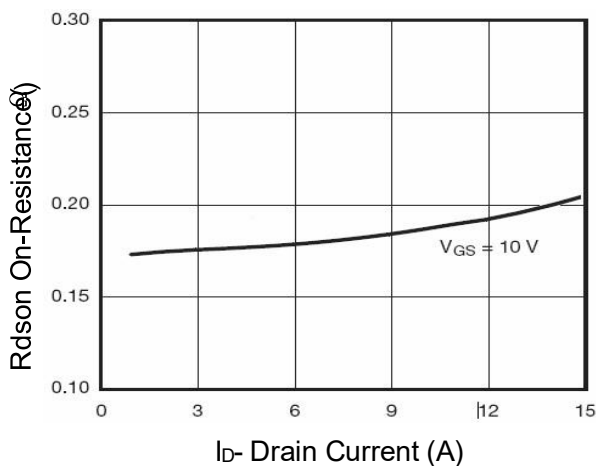
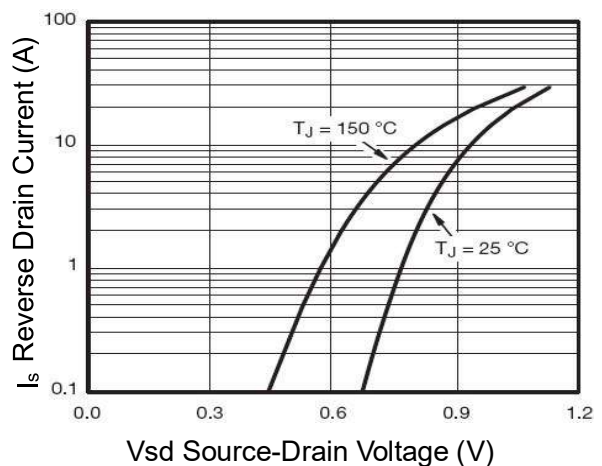


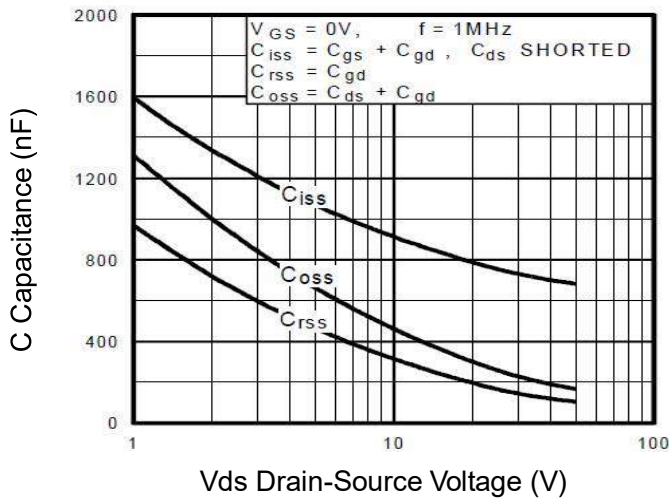
**2) Gate Charge Test Circuit**



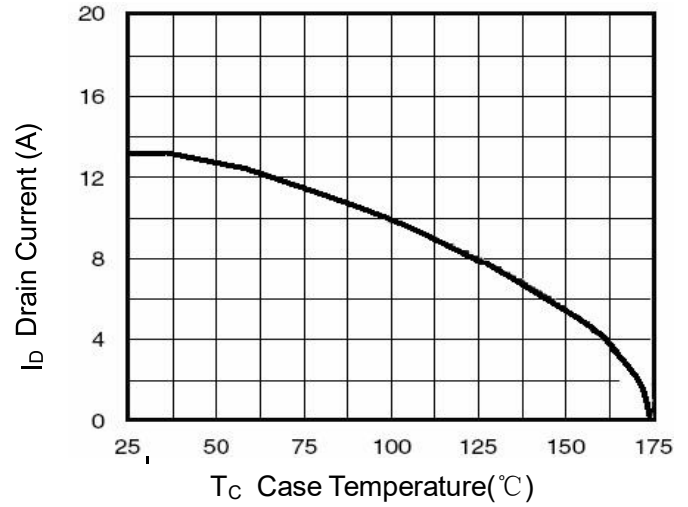
**3) Switch Time Test Circuit**



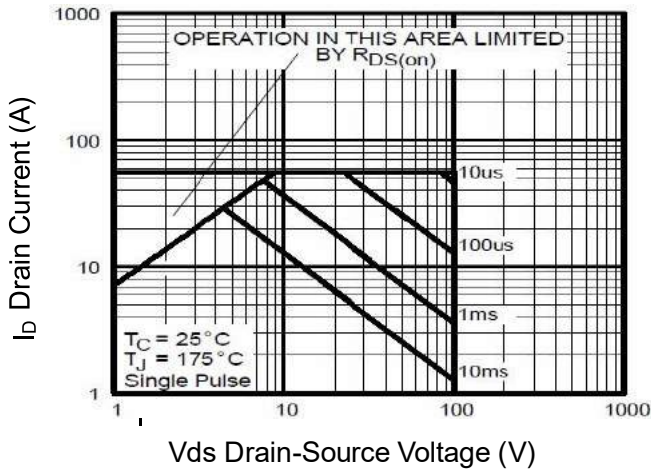
**Typical Electrical and Thermal Characteristics (Curves)**

**Figure 1 Output Characteristics**

**Figure 4 Rds(on)-Junction Temperature**

**Figure 2 Transfer Characteristics**

**Figure 5 Gate Charge**

**Figure 3 Rds(on) Drain Current**

**Figure 6 Source-Drain Diode Forward**



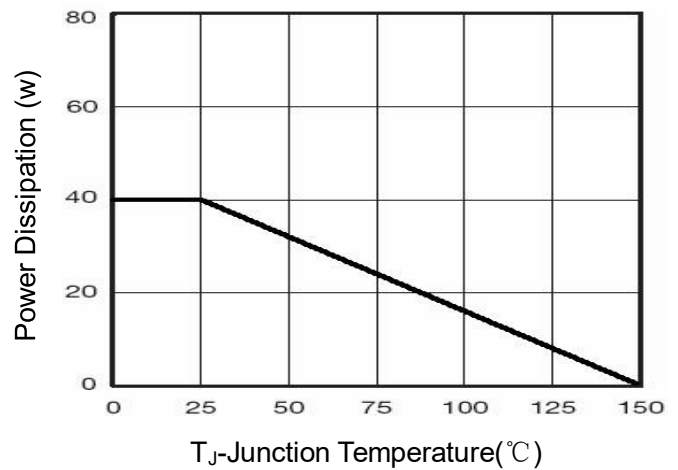
**Figure 7 Capacitance vs Vds**



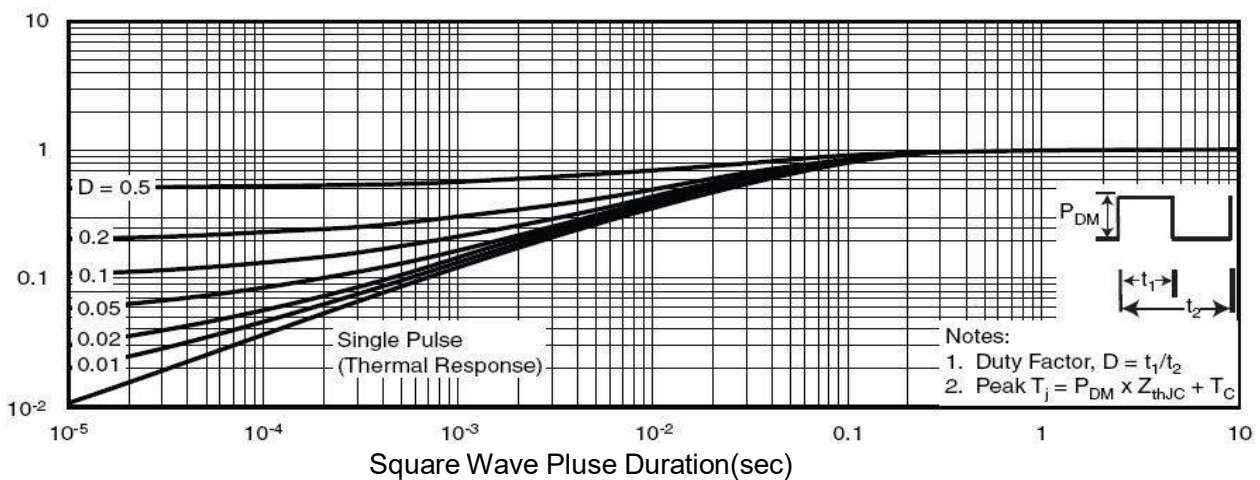
**Figure 9 Drain Current vs Case Temperature**



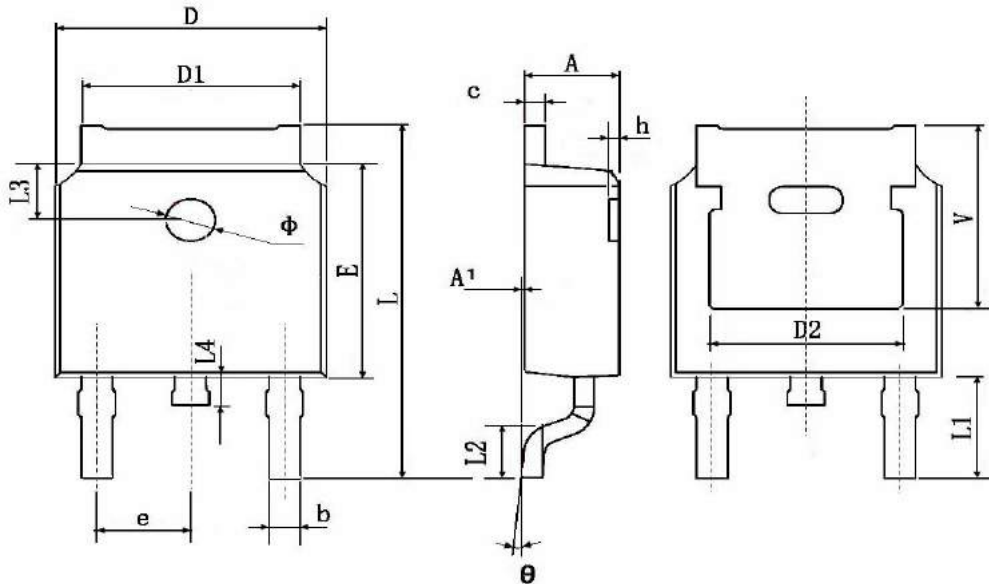
**Figure 8 Safe Operation Area**



**Figure 10 Power De-rating**



**Figure 11 Normalized Maximum Transient Thermal**

**TO252-2L Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	